

METHOD FOR ELIMINATING DEVELOPMENT RELATED DEFECTS
IN PHOTORESIST MASKS

ABSTRACT

Polymer blobs that are development related defects are
5 substantially eliminated in the patterned photoresist masks by
a heat treatment of the wafer performed at the development
step in two different manners according to the present
invention. In the first method, after the development has been
performed as standard, the wafer is heated at 140°C and before
10 cooling takes place, it is rinsed with deionized water (DIW)
at room temperature. In the second method, the wafer is either
developed as standard but rinsed with 60°C DIW instead of 22°C
DIW or, after standard development, it is submitted to an
extra rinse step with 60°C DIW.

15 FIG. 6